

V_{DSS}	30V
$R_{DS(on)}(Max.)$	54mΩ
I_D	±3.5A
P_D	1.5W

●Features

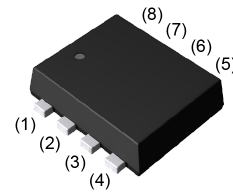
- 1) Low on - resistance.
- 2) Built-in G-S protection diode.
- 3) Small surface mount package(TSMT8)
- 4) Pb-free lead plating ; RoHS compliant

●Application

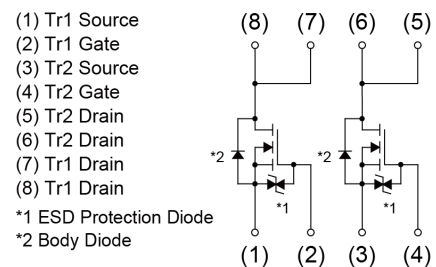
Switching

●Outline

TSMT8



●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	K02

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$) <It is the same ratings for the Tr1 and Tr2>

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	30	V
Continuous drain current		I_D	±3.5	A
Pulsed drain current		$I_{D,pulse}^{*1}$	±12	A
Gate - Source voltage		V_{GSS}	±12	V
Power dissipation	total	P_D^{*2}	1.5	W
	element		1.25	
	total	P_D^{*3}	0.7	
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	-55 to +150	°C

●Thermal resistance

Parameter		Symbol	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction - ambient	total	R_{thJA}^{*2}	-	-	83.3	°C/W
	element		-	-	100	
	total	R_{thJA}^{*3}	-	-	178	

●Electrical characteristics ($T_a = 25^{\circ}\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	29	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	0.5	-	1.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-1.6	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = 4.5V, I_D = 3.5A$	-	38	54	mΩ
		$V_{GS} = 4V, I_D = 3.5A$	-	40	56	
		$V_{GS} = 2.5V, I_D = 3.5A$	-	55	77	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	8	-	Ω
Forward Transfer Admittance	$ Y_{fs} ^{*4}$	$V_{DS} = 10V, I_D = 3.5A$	3.0	-	-	S

●Electrical characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	285	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	90	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	55	-	
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \approx 15V, V_{GS} = 4.5V$	-	8	-	ns
Rise time	t_r^{*4}	$I_D = 1.7A$	-	12	-	
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L = 8.8\Omega$	-	29	-	
Fall time	t_f^{*4}	$R_G = 10\Omega$	-	13	-	

●Gate charge characteristics ($T_a = 25^\circ\text{C}$) <It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*4}	$V_{DD} \approx 15V$	-	4.6	-	nC
Gate - Source charge	Q_{gs}^{*4}	$I_D = 3.5A$	-	0.7	-	
Gate - Drain charge	Q_{gd}^{*4}	$V_{GS} = 4.5V$	-	1.5	-	

●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S	$T_a = 25^\circ\text{C}$	-	-	1	A
Body diode pulse current	I_{SP}^{*1}		-	-	12	
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0V, I_S = 3.5A$	-	-	1.2	V

 *1 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board (30×30×0.8mm)

*3 Mounted on a FR4 (20×20×0.8mm)

*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

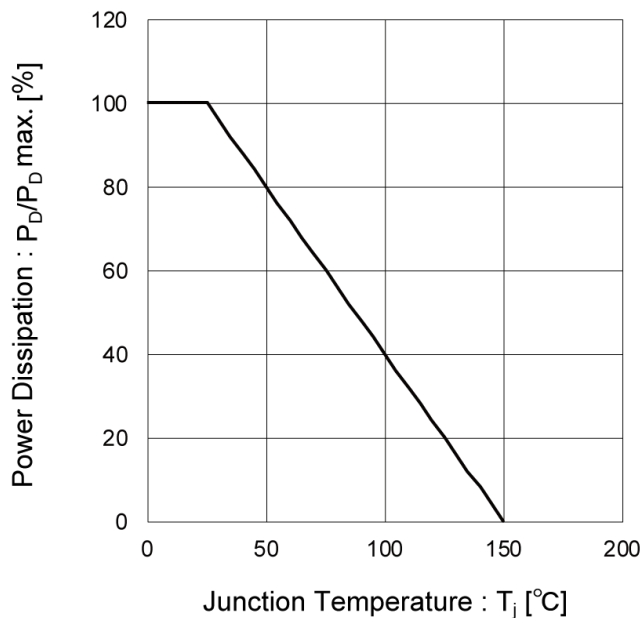


Fig.2 Maximum Safe Operating Area

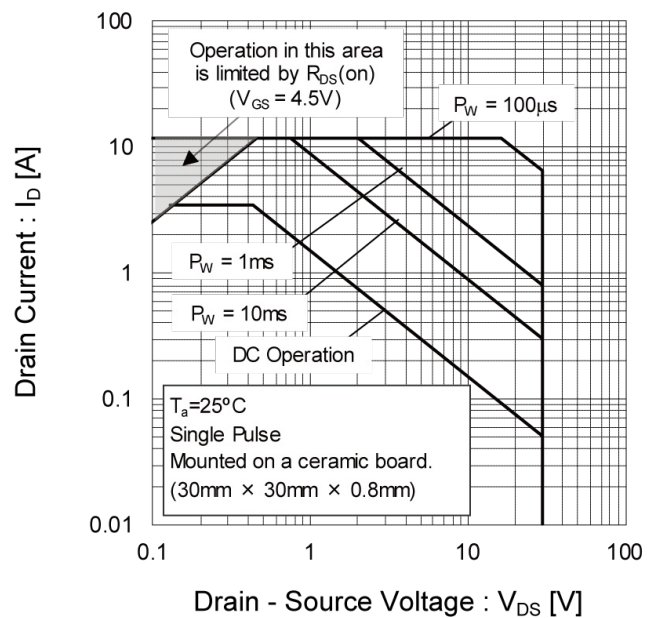


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

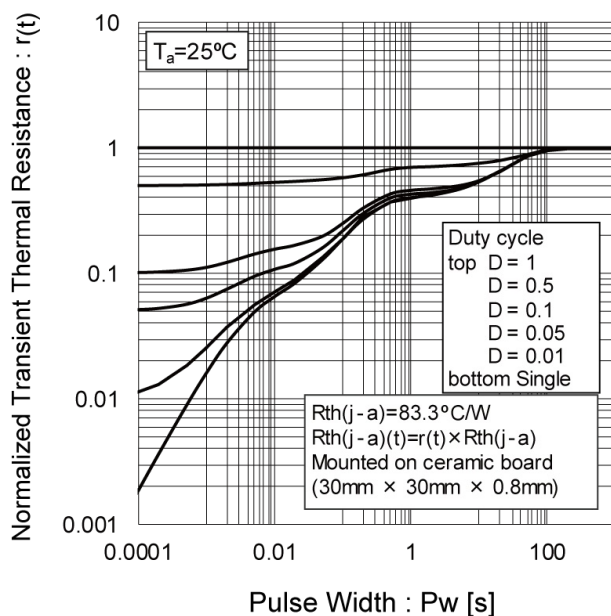
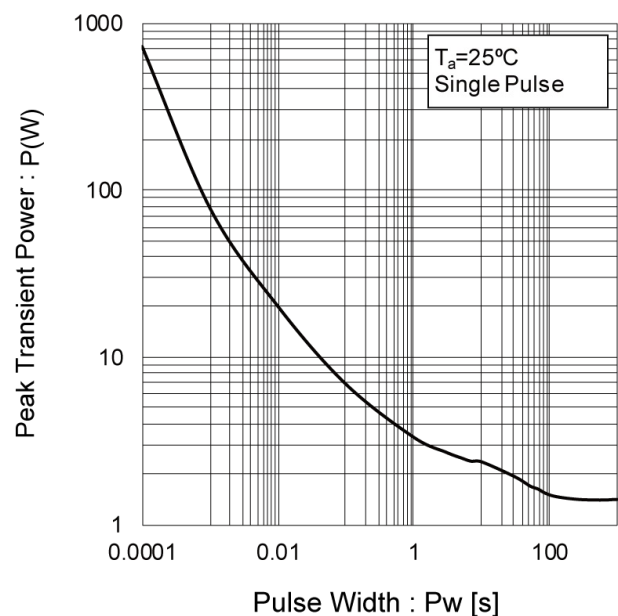


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

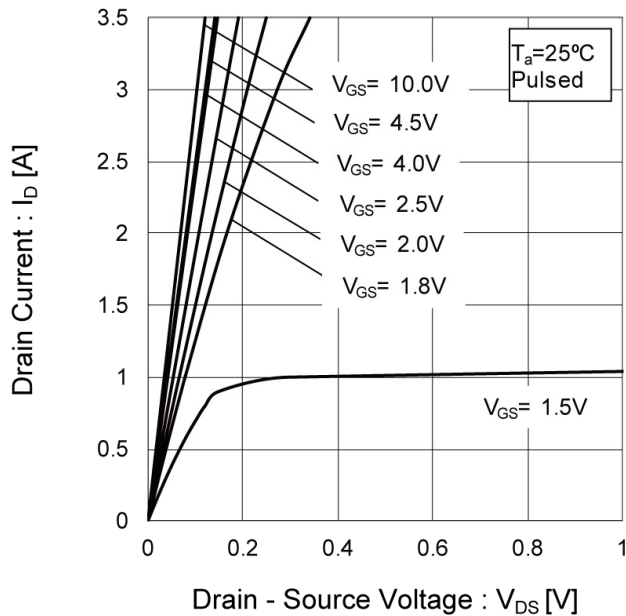


Fig.6 Typical Output Characteristics(II)

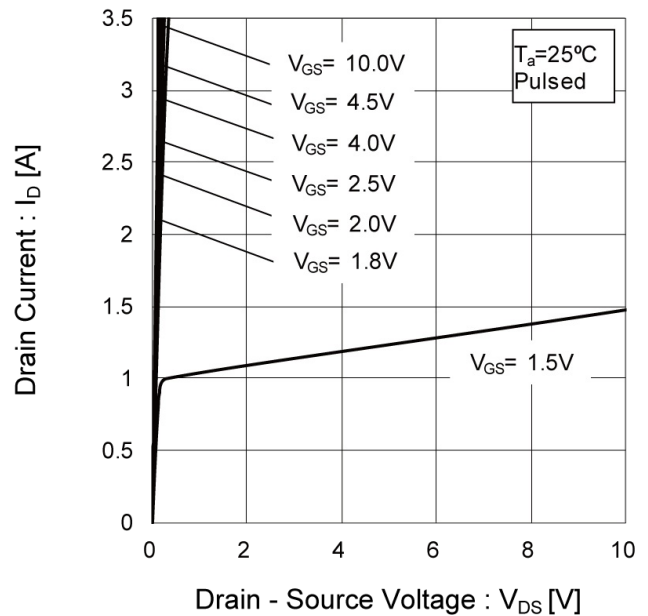


Fig.7 Breakdown Voltage vs. Junction Temperature

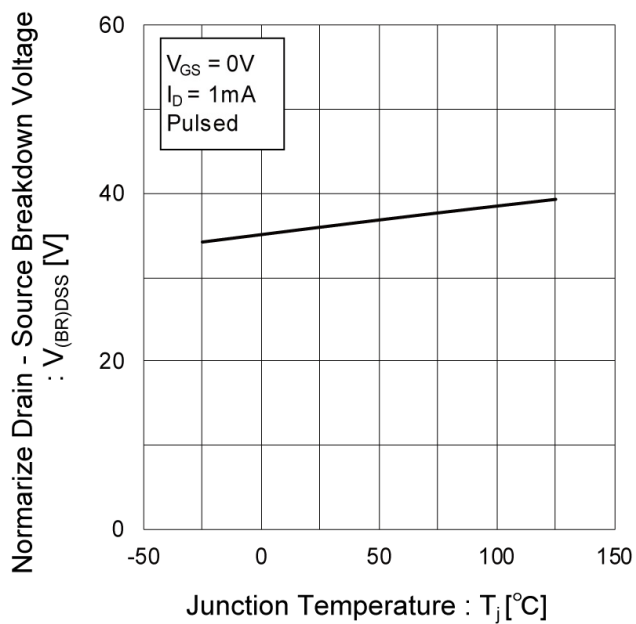
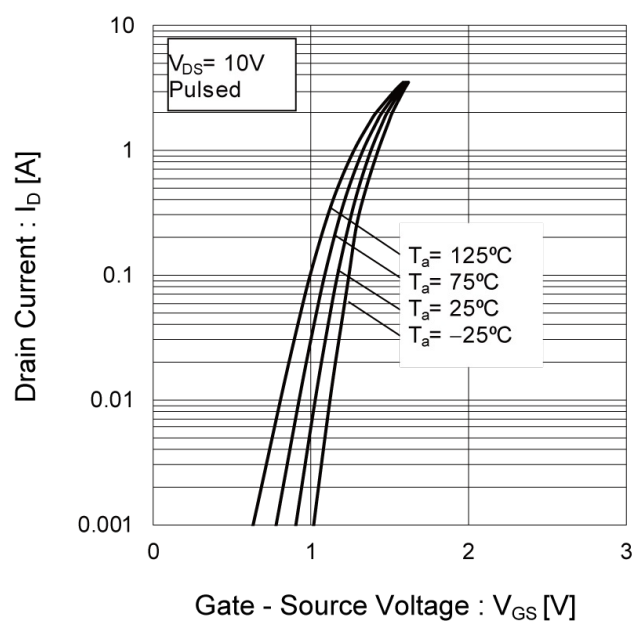


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs.
Junction Temperature

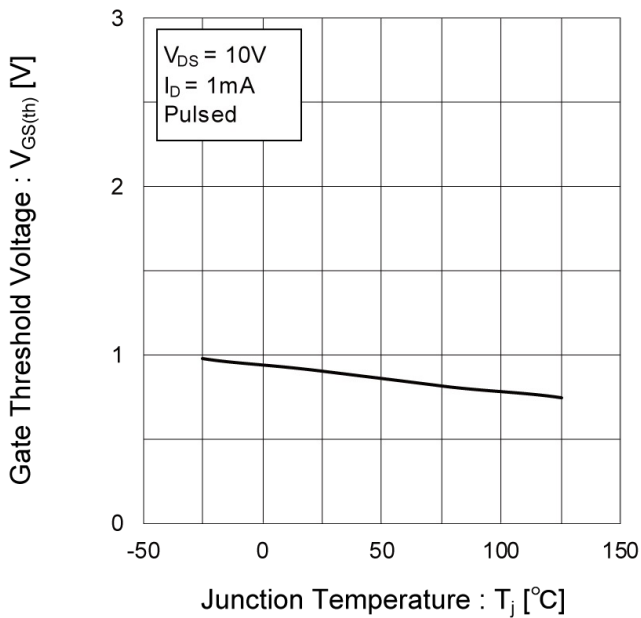


Fig.10 Forward Transfer Admittance vs.
Drain Current

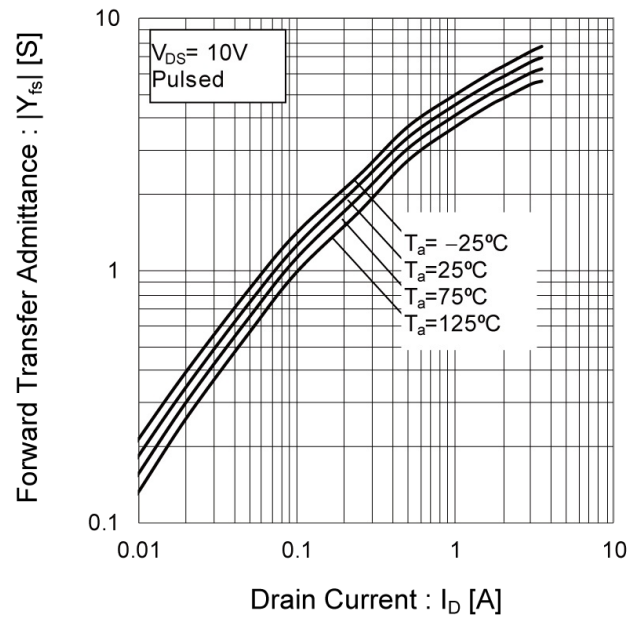


Fig.11 Drain Current Derating Curve

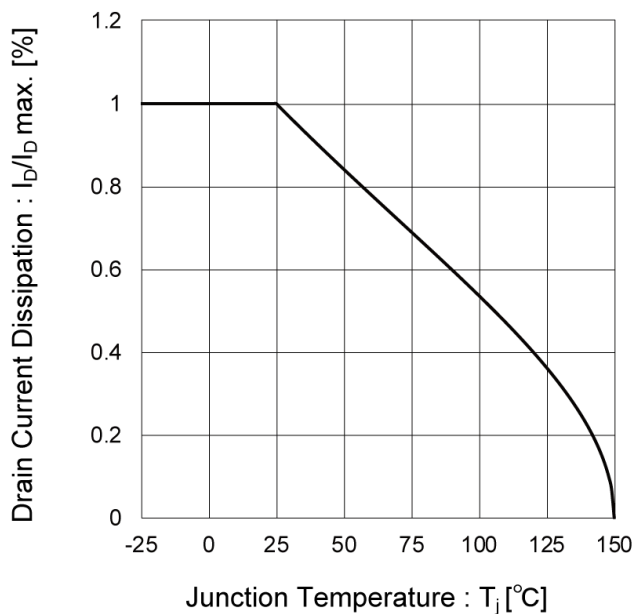
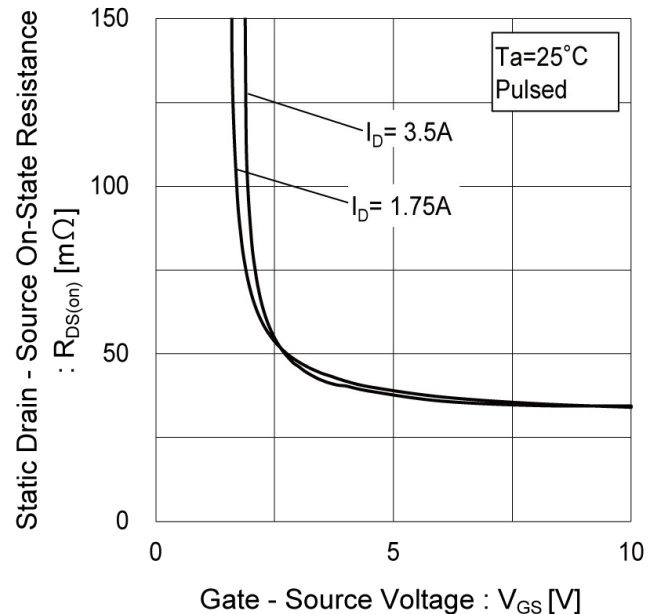


Fig.12 Static Drain - Source On - State
Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

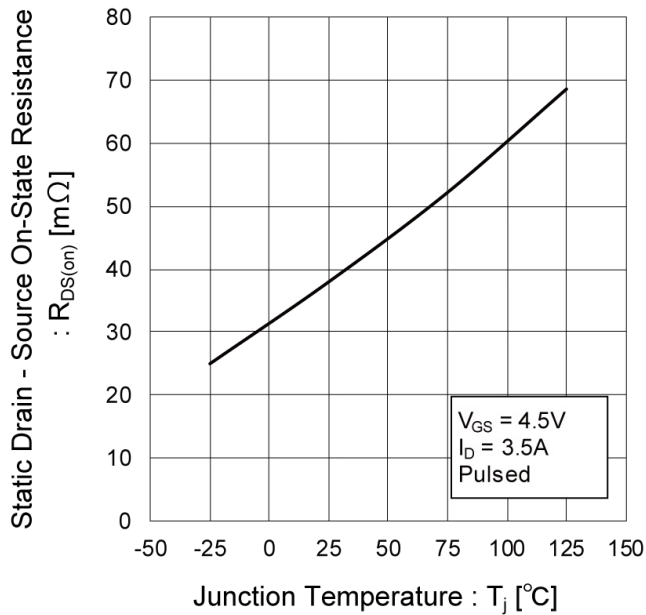
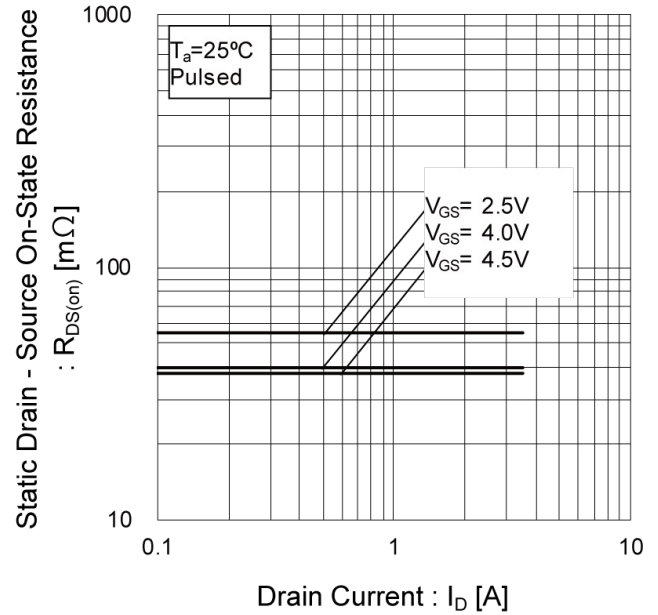


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State
Resistance vs. Drain Current (II)

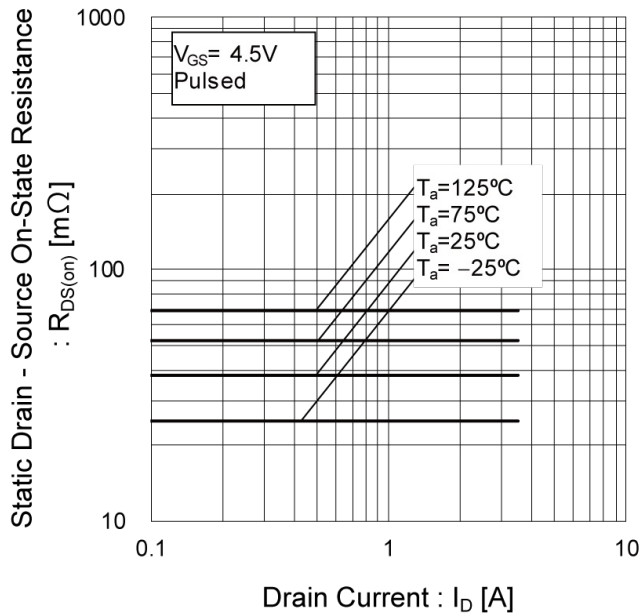


Fig.16 Static Drain - Source On - State
Resistance vs. Drain Current (III)

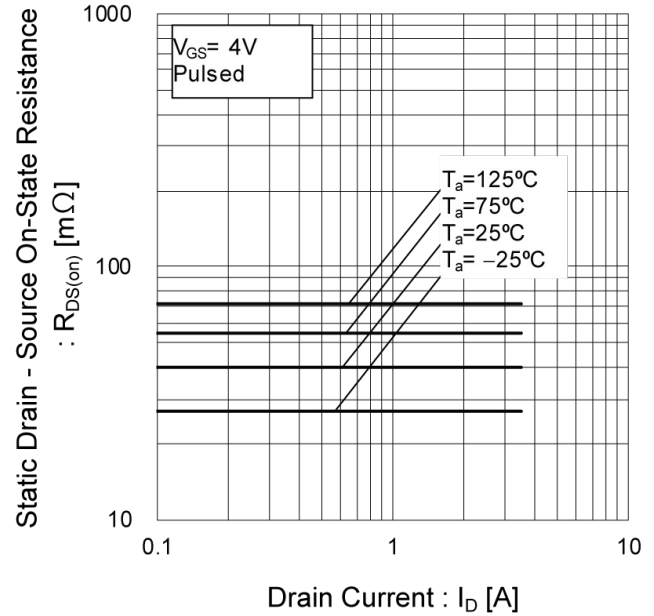
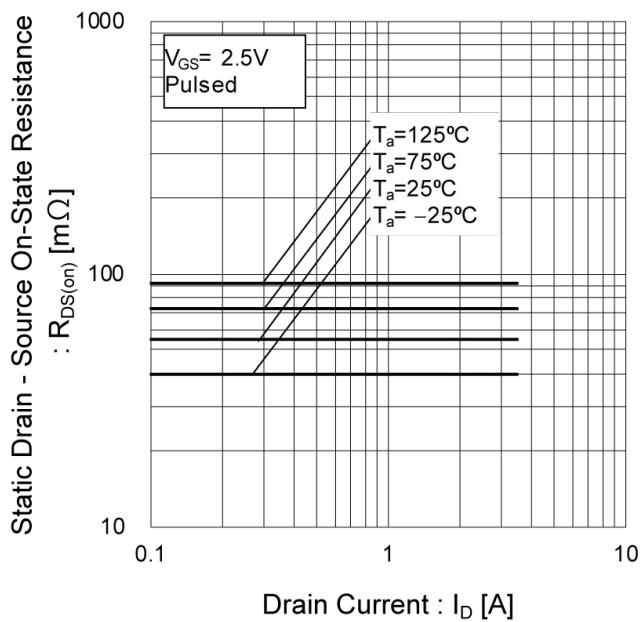


Fig.17 Static Drain - Source On - State
Resistance vs. Drain Current (IV)



●Electrical characteristic curves

Fig.18 Typical Capacitance vs.
Drain - Source Voltage

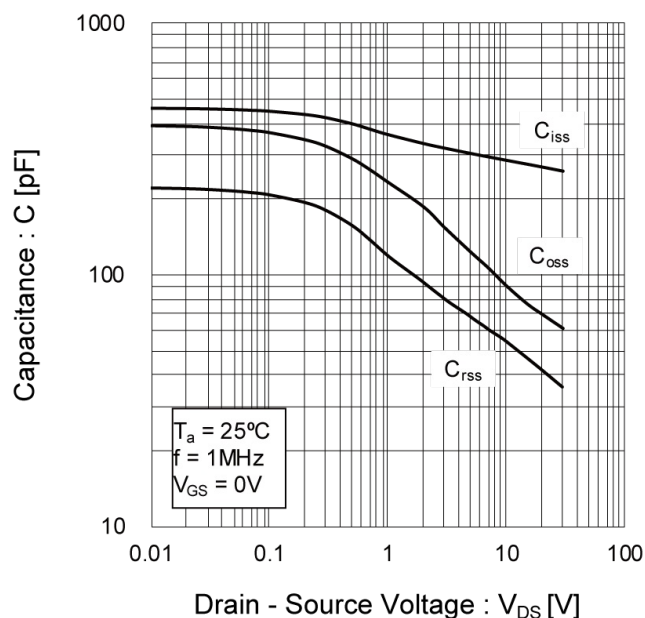


Fig.19 Switching Characteristics

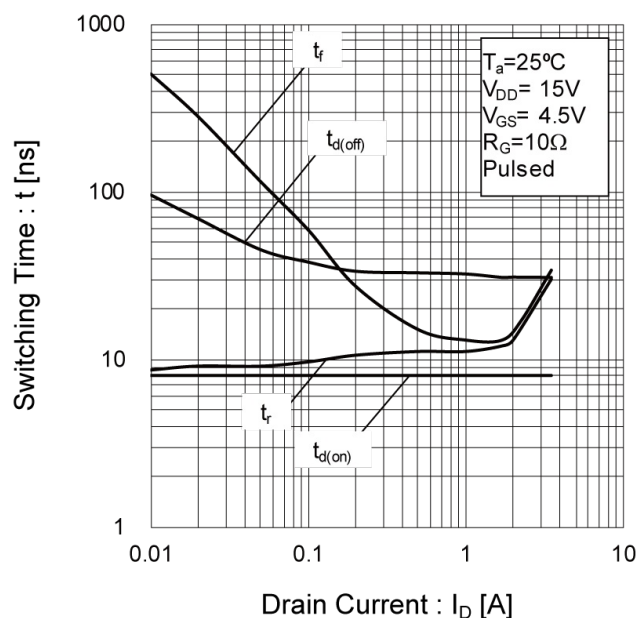


Fig.20 Dynamic Input Characteristics

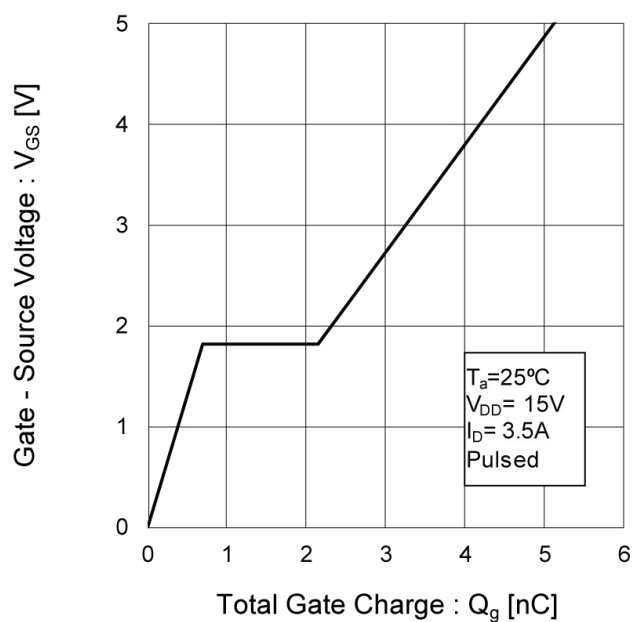
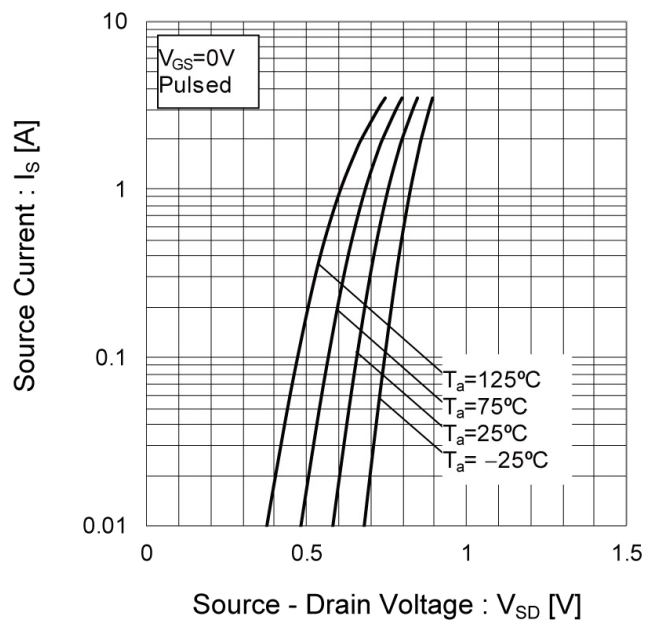


Fig.21 Source Current vs.
Source Drain Voltage



●Measurement circuits <It is the same for the Tr1 and Tr2>

Fig. 1-1 SWITCHING TIME MEASUREMENT CIRCUIT

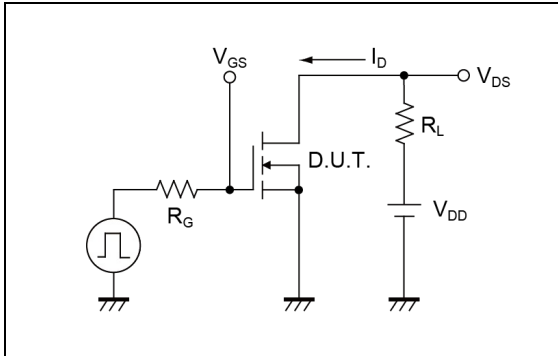


Fig. 1-2 SWITCHING WAVEFORMS

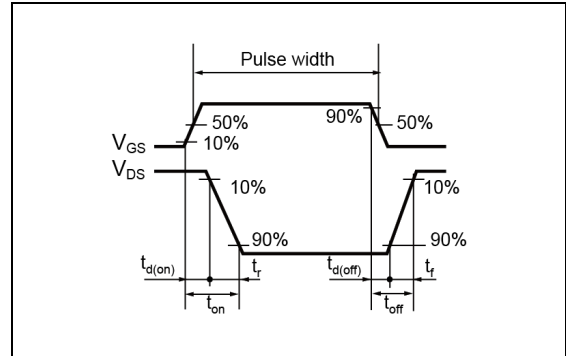


Fig. 2-1 GATE CHARGE MEASUREMENT CIRCUIT

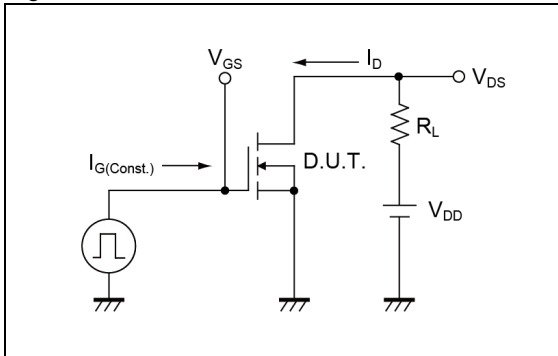
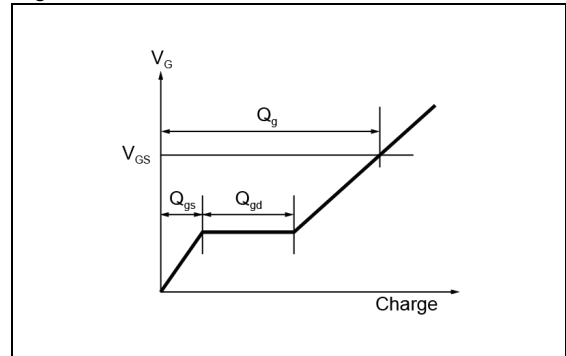
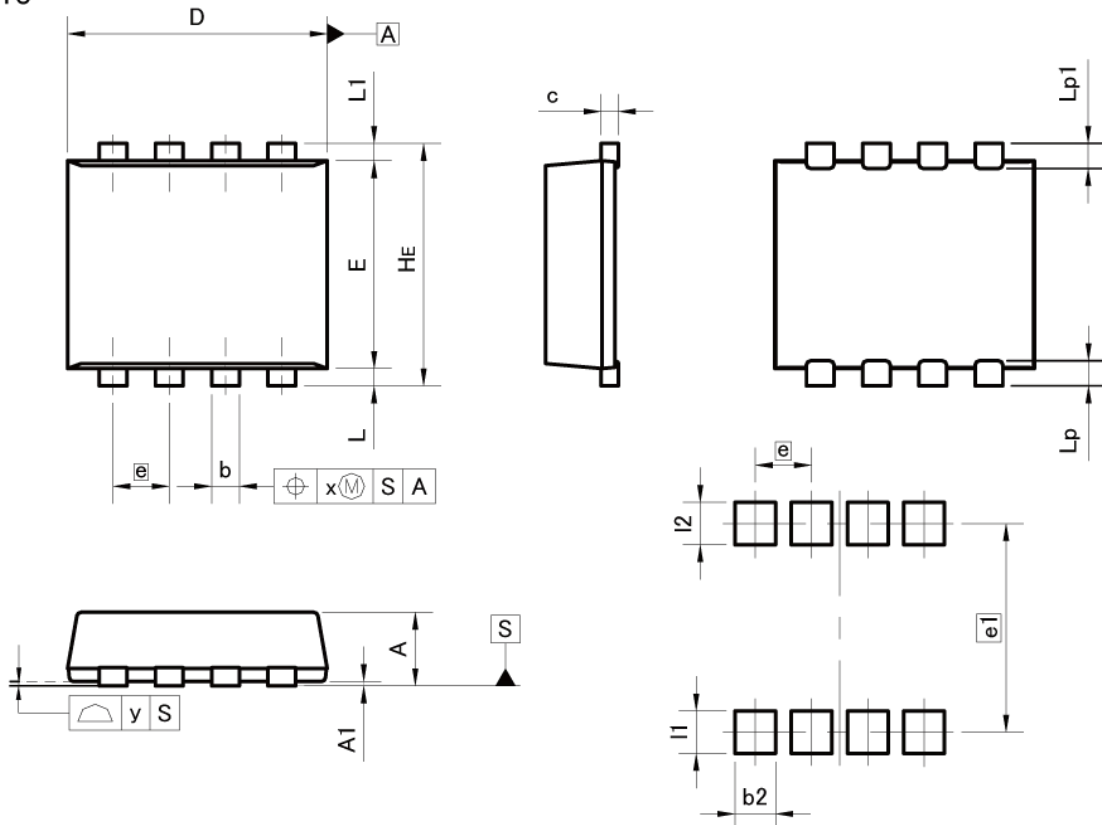


Fig. 2-2 GATE CHARGE WAVEFORM



●Dimensions

TSMT8



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.47	—	0.019
e1	2.41		0.095	
I1	—	0.49	—	0.019
I2	—	0.49	—	0.019

Dimension in mm/inches

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